

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### FEATURES

- Suitable for VSAT, UNII radio applications
- High Power  $P_{1dB}=31.7\text{dBm(MIN.)}$
- High Power Added Efficiency  $\eta_{add}=21\%(TYP.)$
- High Gain  $G_{1dB}=26.7\text{dB(MIN.)}$
- Broadband Operation  $f=5.8\text{-}6.475\text{GHz.}$

#### ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

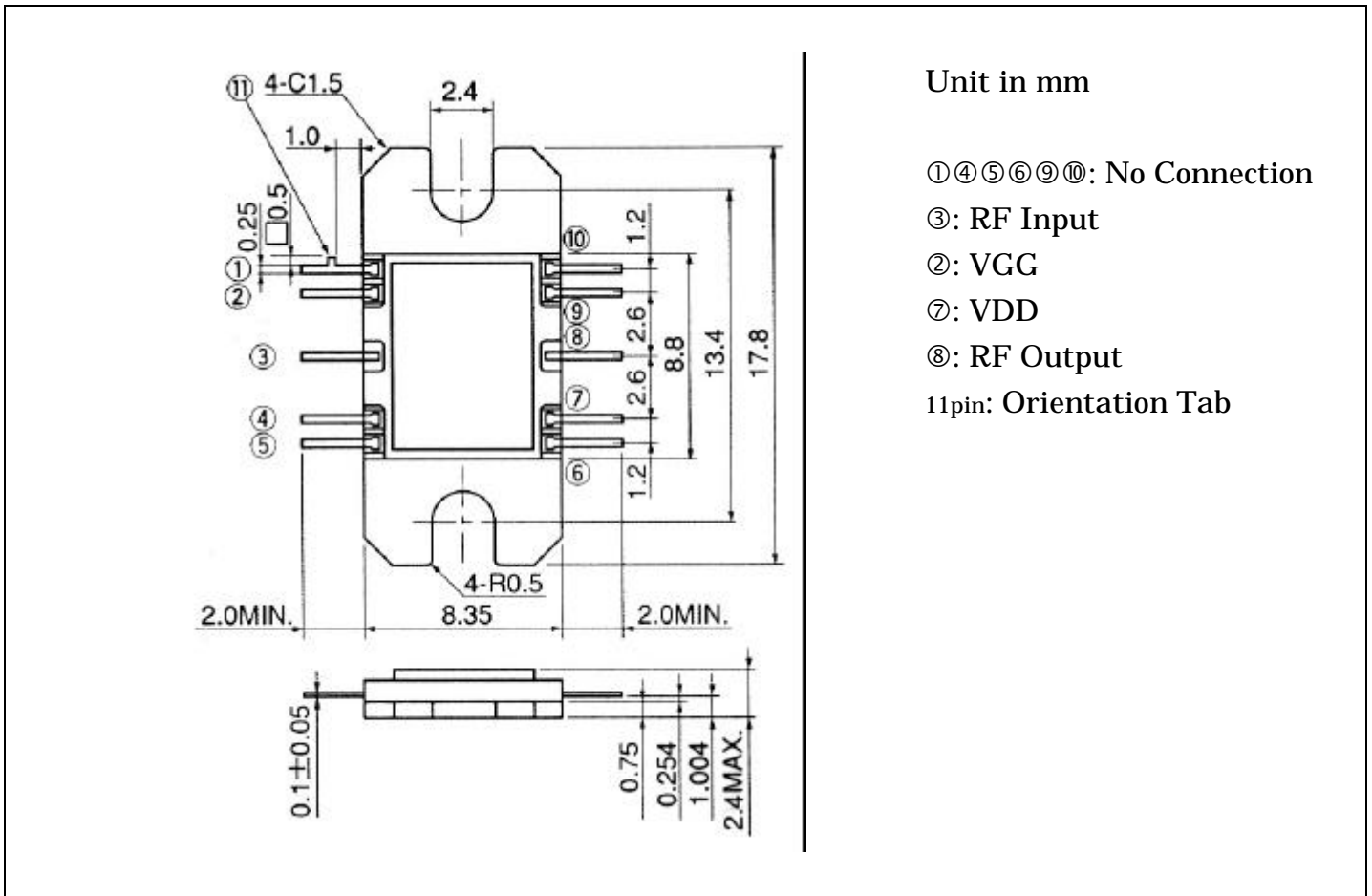
CHARACTERISTICS	SYMBOL	UNIT	RATINGS
DRAIN SUPPLY VOLTAGE	VDD	V	15
GATE SUPPLY VOLTAGE	VGG	V	-10
INPUT POWER	Pin	dBm	10
FLANGE TEMPERATURE	Tf	°C	-30 - +80
STORAGE TEMPERATURE	Tstg	°C	-65 - +175

#### RF PERFORMANCE SPECIFICATIONS ( $T_a=25^\circ\text{C}$ )

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.	
Operating Frequency	f	VDD=10V VGG=-5V	GHz	5.8	-	6.475	
Output Power at 1dB Gain Compression Point	$P_{1dB}$		dBm	31.7	-	-	
Power Gain at 1dB Gain Compression Point	$G_{1dB}$		dB	26.7	-	-	
Gain Flatness	$\Delta G$		dB	-	-	+/- 2.0	
Drain Current	IDD		A	-	1.2	1.6	
Power Added Efficiency	$\eta_{add}$		%	-	21	-	
VSWRin (small signal)	VSWRin		-	-	-	2.0:1	3.0:1

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**Package Outline**



**Recommended Bias Configuration**

